

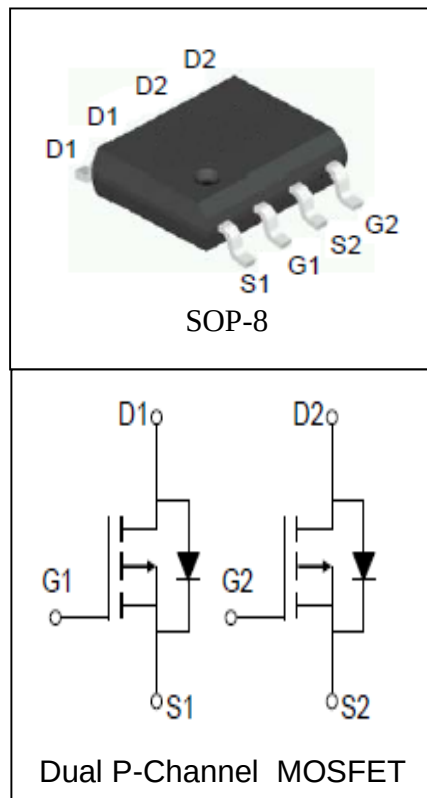
Features

- -30V/-4.8A,
 $R_{DS(ON)} = 50m\Omega$ (Typ.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 80m\Omega$ (Typ.) @ $V_{GS} = -4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Available

Applications

- Power Management.

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _A =25°C	-2.5	A
Mounted on Large Heat Sink				
I _{DP}	300μs Pulse Drain Current Tested	T _A =25°C	-18 ^①	A
I _D	Continuous Drain Current	T _A =25°C	-4.8	A
		T _A =70°C	-3.8	
P _D	Maximum Power Dissipation	T _A =25°C	2	W
		T _A =70°C	1.3	
R _{θJA} ^②	Thermal Resistance-Junction to Ambient		62.5	°C/W

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU30S4H			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	μA
		T _J =85°C			-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1	-1.8	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ③	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-5A		50	60	mΩ
		V _{GS} =-4.5V, I _{DS} =-3A		80	100	mΩ
Diode Characteristics						
V _{SD} ③	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V			-1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-4A, dI _{SD} /dt=100A/μs		15		ns
Q _{rr}	Reverse Recovery Charge			9		nC
Dynamic Characteristics ④						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz		490		pF
C _{oss}	Output Capacitance			85		
C _{rss}	Reverse Transfer Capacitance			40		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _L =3.75Ω, I _{DS} =-4A, V _{GEN} =-10V, R _G =3Ω		9		ns
t _r	Turn-on Rise Time			15		
t _{d(OFF)}	Turn-off Delay Time			27		
t _f	Turn-off Fall Time			11		
Gate Charge Characteristics ④						
Q _g	Total Gate Charge	V _{DS} =-24V, V _{GS} =-10V, I _{DS} =-4A		10		nC
Q _{gs}	Gate-Source Charge			1.9		
Q _{gd}	Gate-Drain Charge			3.2		

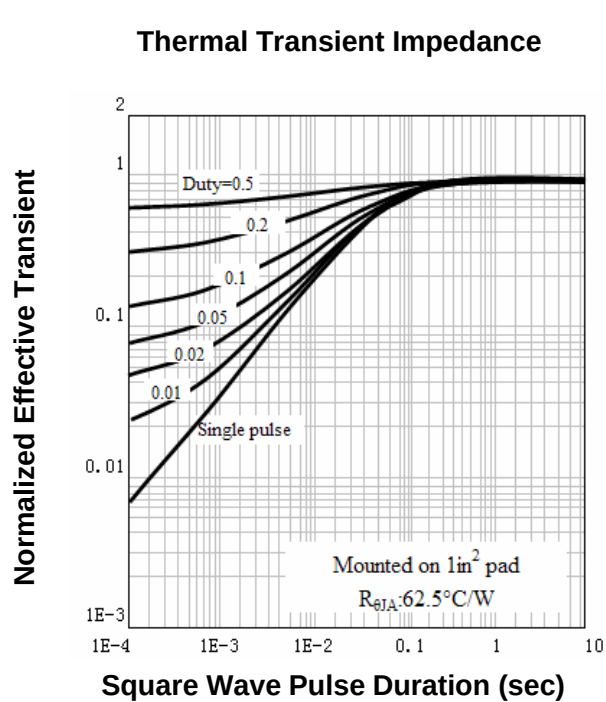
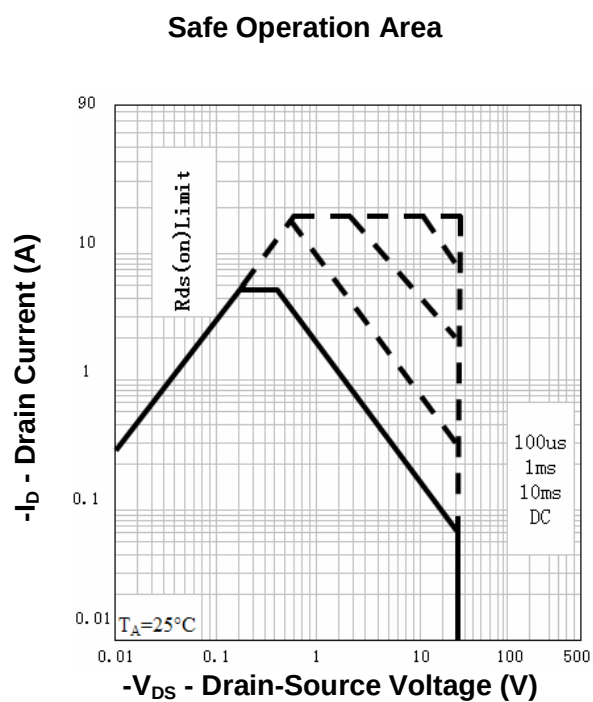
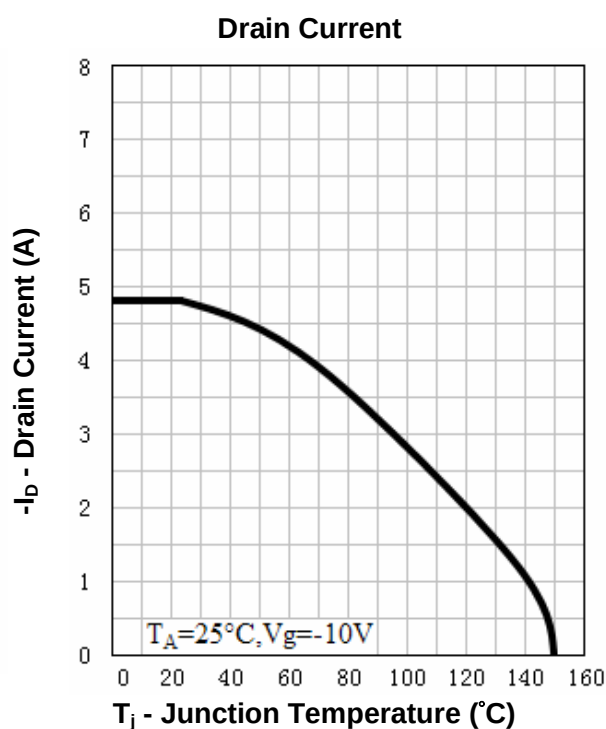
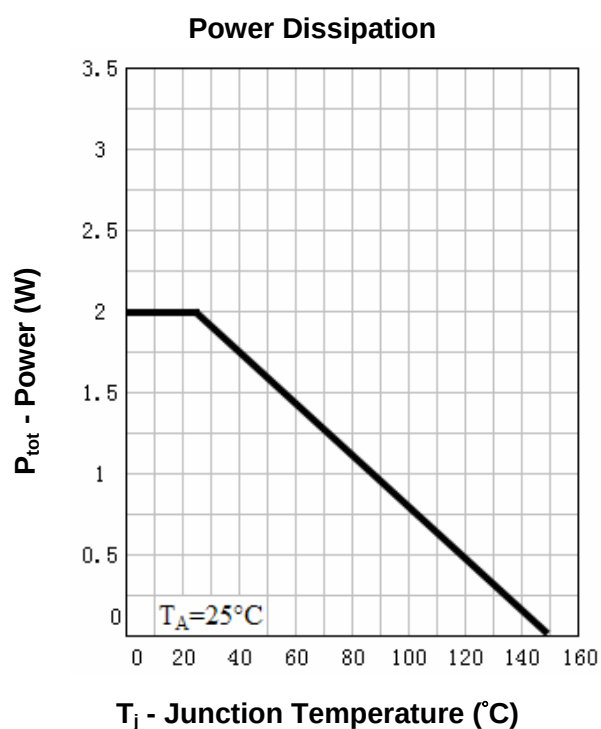
Notes: ① Pulse width limited by safe operating area.

② When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.

③ Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

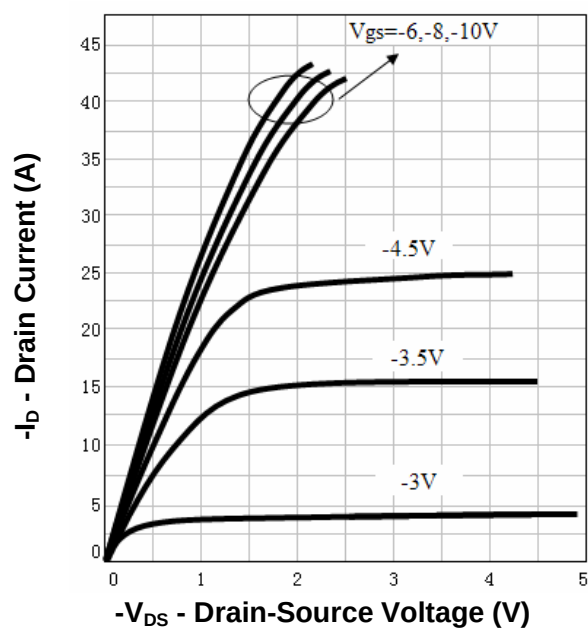
④ Guaranteed by design, not subject to production testing.

Typical Characteristics

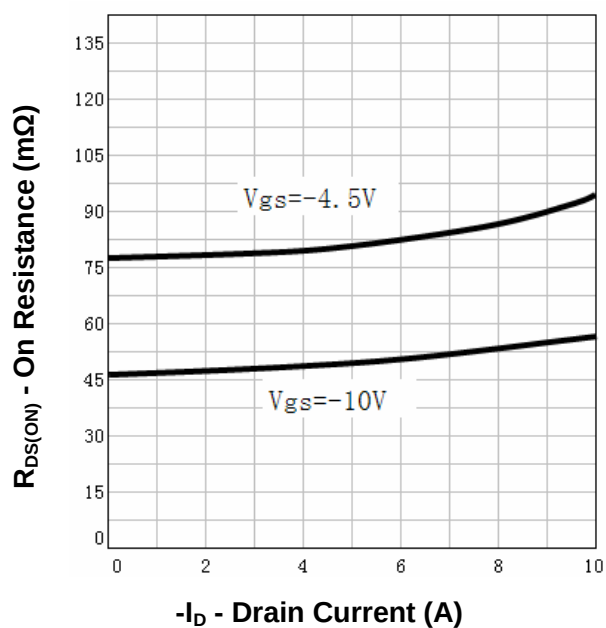


Typical Characteristics

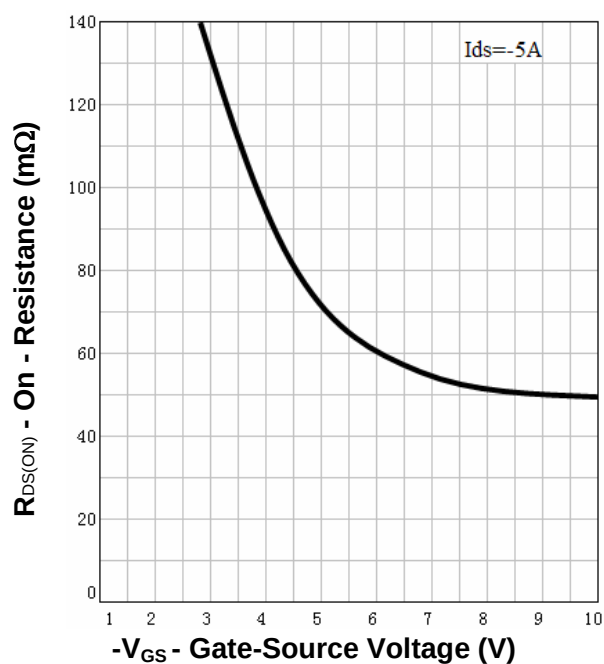
Output Characteristics



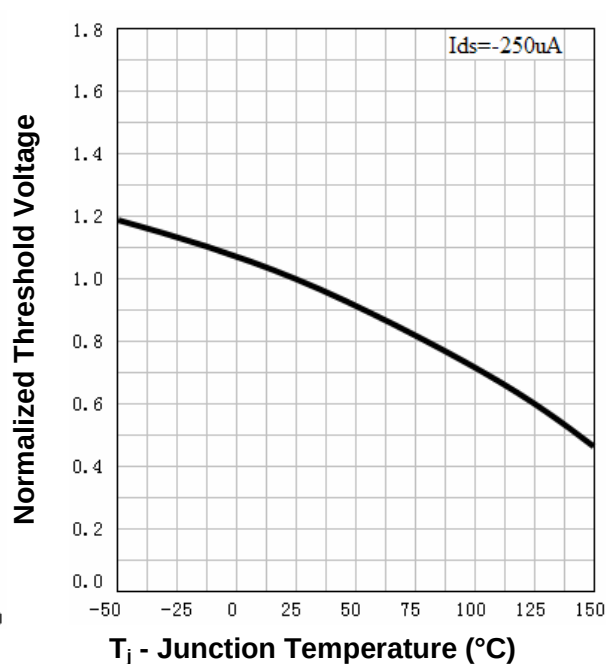
Drain-Source On Resistance



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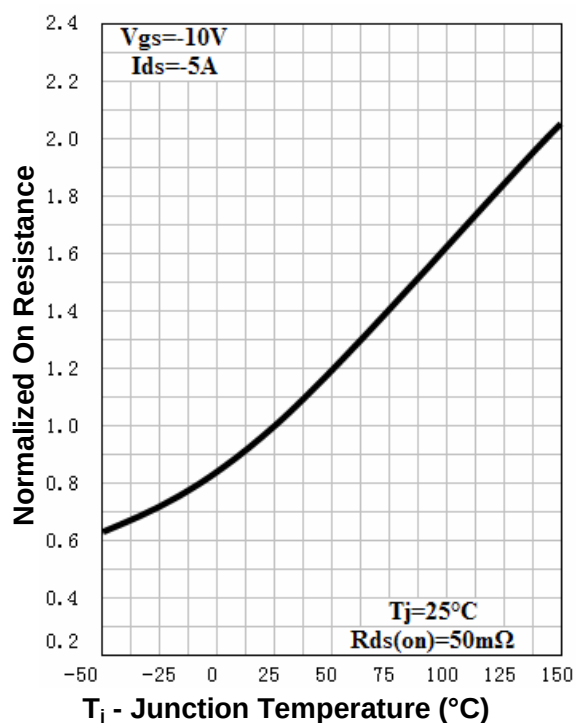


Gate Threshold Voltage

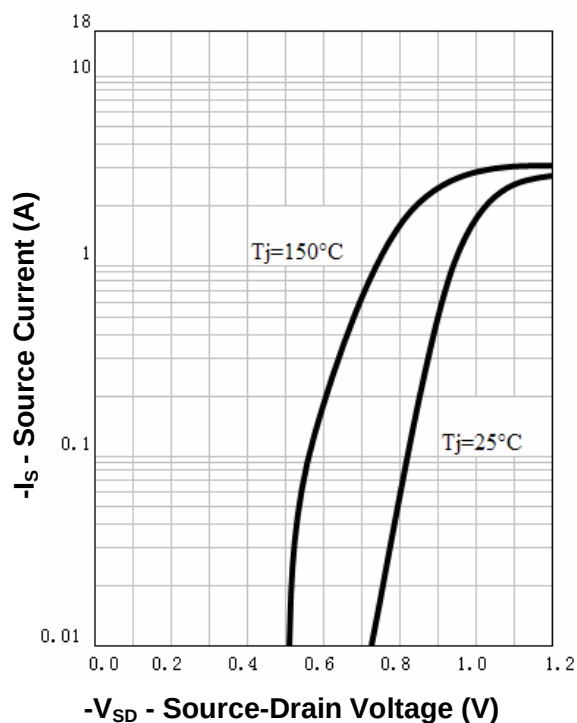


Typical Characteristics

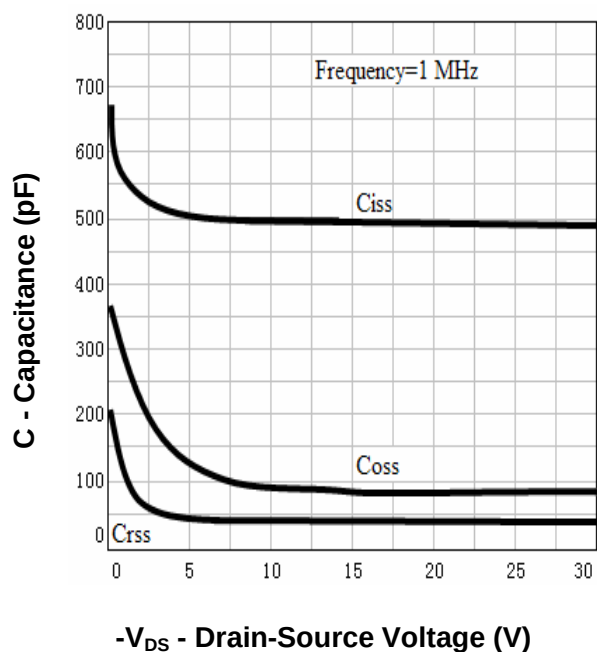
Drain-Source On Resistance



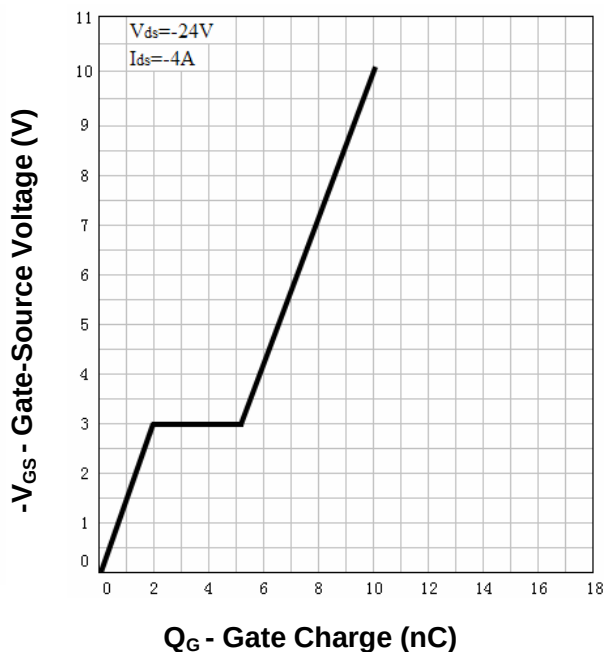
Source-Drain Diode Forward



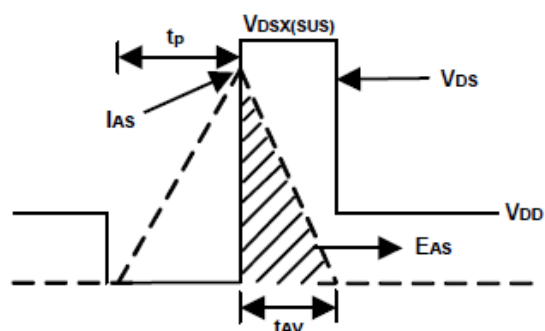
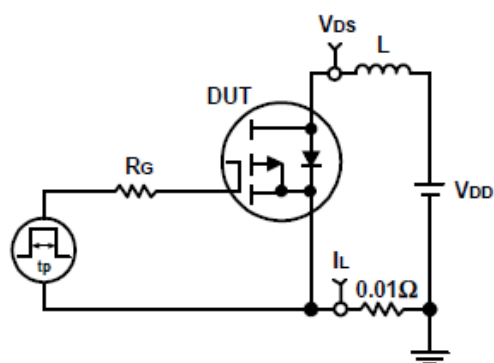
Capacitance



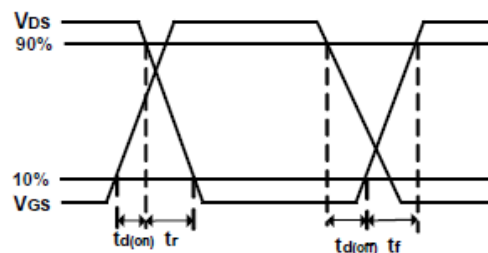
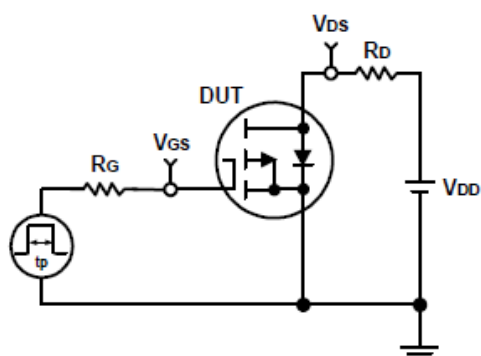
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

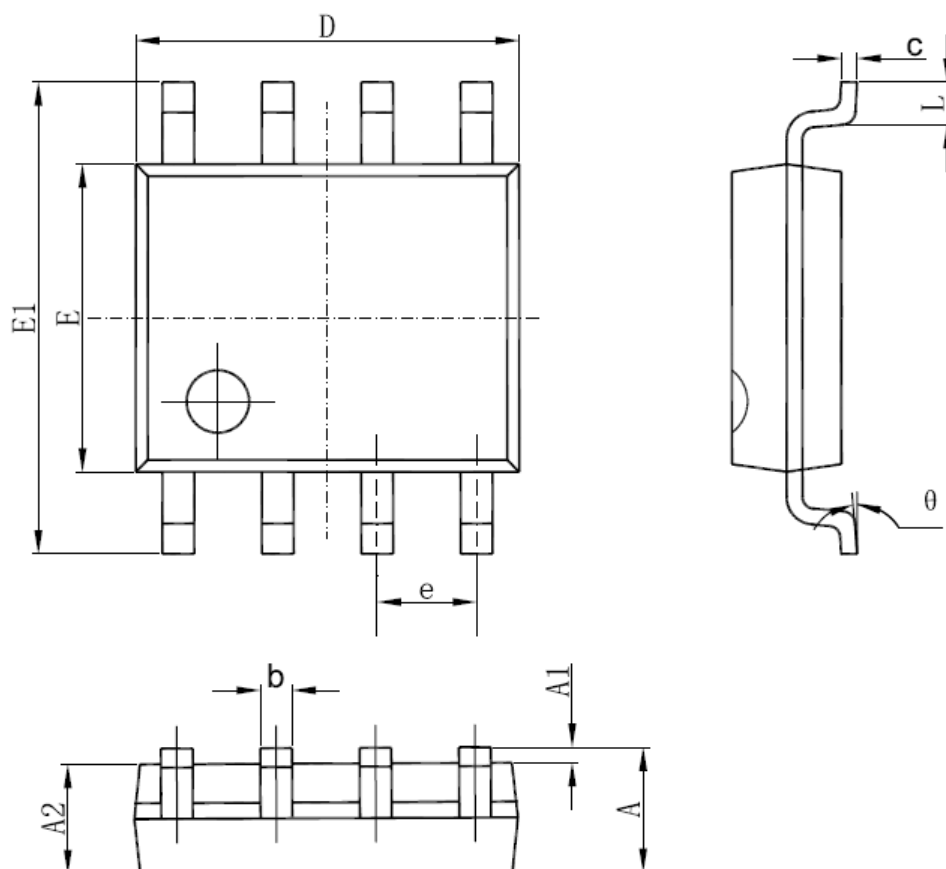


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU30S4H	RU30S4H	SOP-8	Tape&Reel	2500	13''	12mm

Package Information

SOP-8



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.350	1.750	0.053	0.069	E	3.800	4.000	0.150	0.157
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	1.270 (BSC)		0.050 (BSC)	
b	0.330	0.510	0.013	0.020	L	0.400	1.270	0.016	0.050
c	0.170	0.250	0.006	0.010	θ	0°	8°	0°	8°
D	4.700	5.100	0.185	0.200					

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

Room 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA

TEL: (86-755) 8311-5334

FAX: (86-755) 8311-4278

E-mail: Sales-SZ@ruichips.com